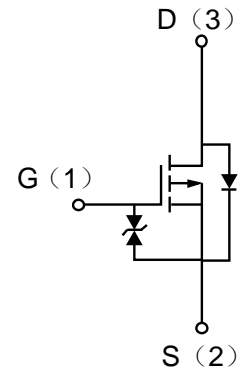


Description

The enhancement mode MOS is extremely high density cell and low on-resistance.

MOSFET Product Summary		
$V_{DS}(V)$	$R_{DS(on)}(\Omega)$	$I_D(A)$
-20	0.037 @ $V_{GS}=-4.5V$	-4



Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current Continuous	I_D	-4	A
Pulsed Drain Current (Note 1)	I_{DM}	-30	A
Total Power Dissipation	P_D	1.4	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Thermal resistance

Parameter	Symbol	Typ.	Units
Maximum Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89.3	°C/W

Electrical characteristics per line @25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D = -250\mu A, V_{GS} = 0V$	-20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$	-	-	-1.0	μA
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$	-	-	± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.65	-1.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -4A$	-	0.037	0.047	Ω
		$V_{GS} = -2.5V, I_D = -4A$	-	0.049	0.060	Ω
Forward Trans conductance	g_{FS}	$V_{DS} = -5V, I_D = -4A$	8	-	-	S
Total Gate Charge	Q_g	$I_D = -4A, V_{DS} = -10V, V_{GS} = -4.5V$	-	17	-	nC
Gate-to-Source Charge	Q_{gs}		-	1.2	-	
Gate-to-Drain(Miller) Charge	Q_{gd}		-	4.3	-	
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -10V, f = 1MHz$	-	1250	-	pF
Output Capacitance	C_{DSS}		-	200	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	155	-	pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10V, V_{GS} = -4.5V, R_L = 2.5\Omega, R_{GEN} = 3\Omega$	-	9.3	-	ns
Rise Time	t_r		-	15	-	
Turn-Off Delay Time	$t_{d(off)}$		-	80	-	
Fall Time	t_f		-	25	-	
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS} = 0V, I_S = -1A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-2.2	A

Note1: Repetitive Rating: Pulse width limited by maximum junction temperature.

Note2: Surface Mounted on FR4 Board, $t \leq 10sec$.

Note3: Pulse Test Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

Typical Characteristics

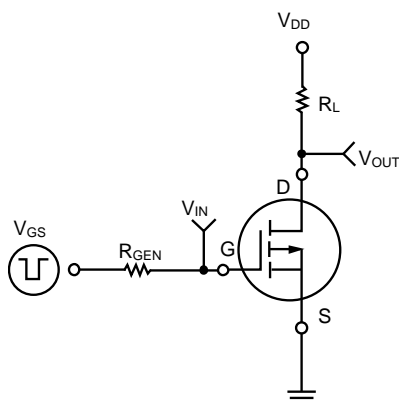


Figure 1. Switching Test Circuit

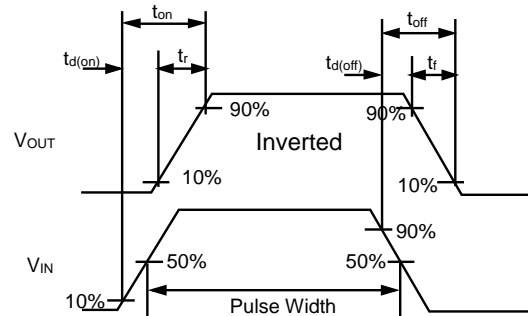


Figure 2. Switching Waveforms

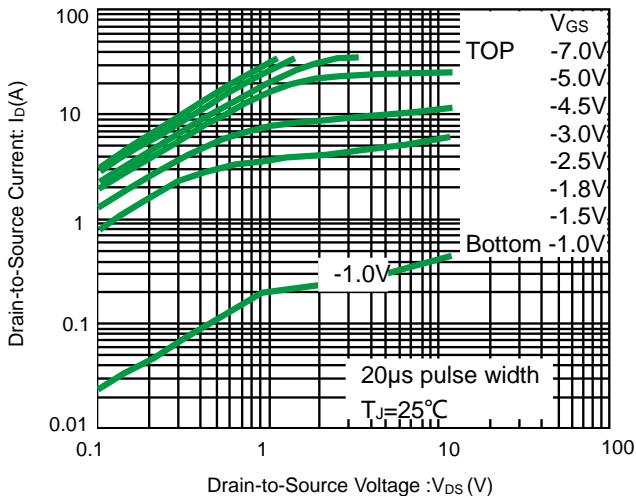


Fig 3. Typical output characteristics

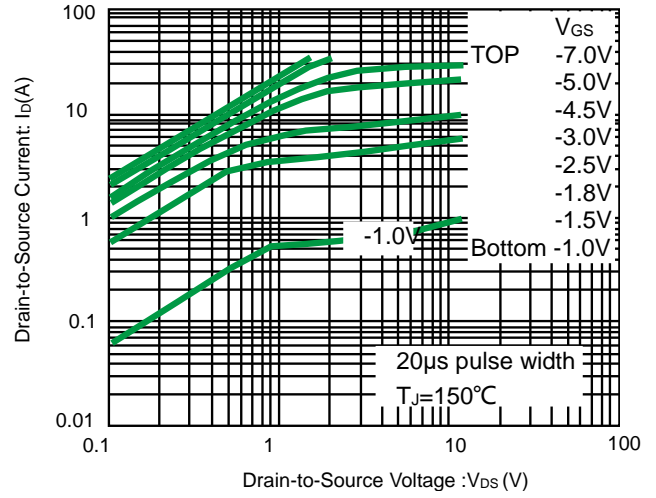


Fig 4. Typical output characteristics

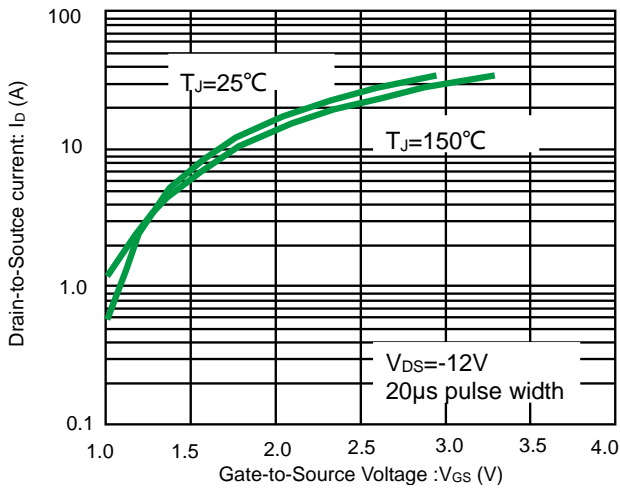


Fig 5. Typical transfer characteristics

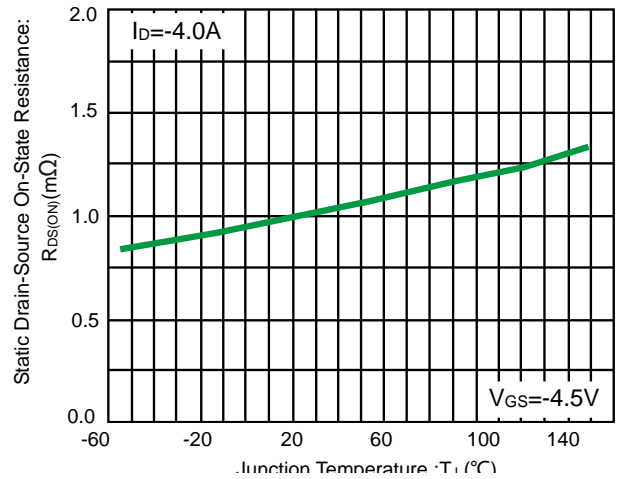


Fig 6. Normalized On-Resistance vs, Temperature

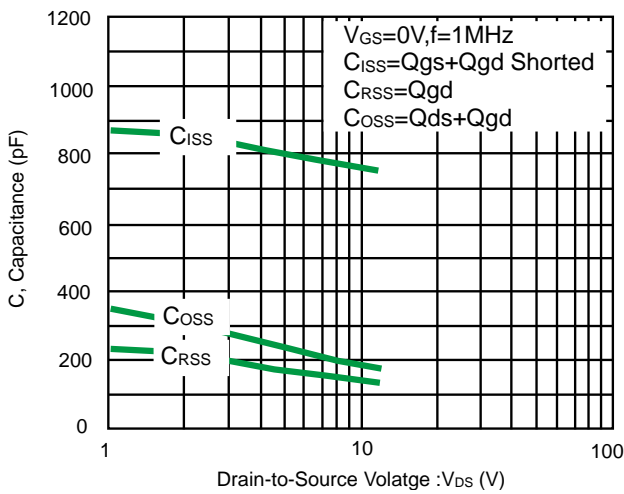


Fig 7. Typical Capacitance vs. Drain-to-Source voltage

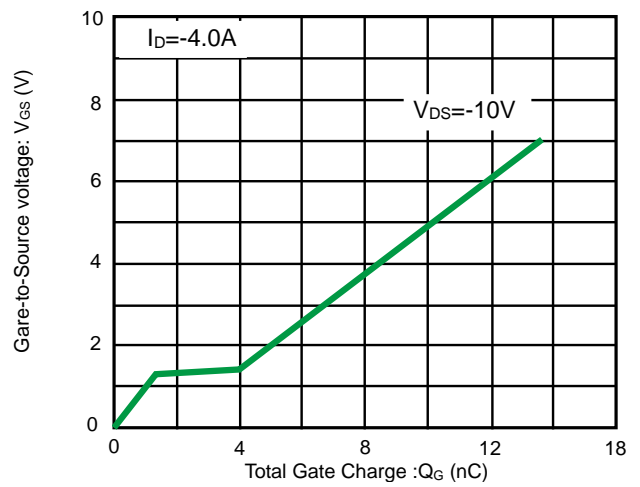


Fig 8. Typical Gate Charge vs. Gate-to-Source voltage

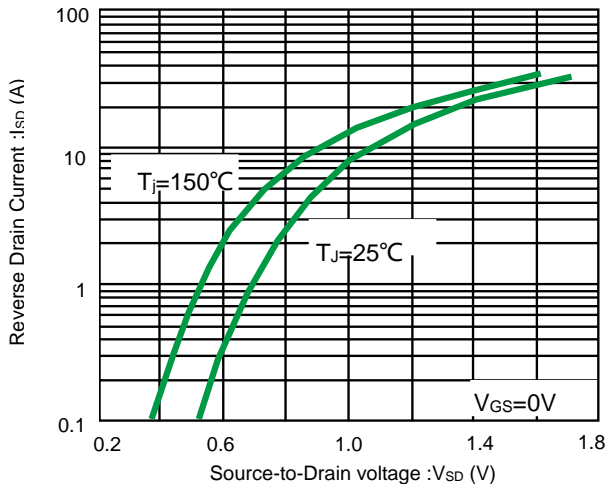


Fig 9. Typical Source-Drain Diode Forward Voltage

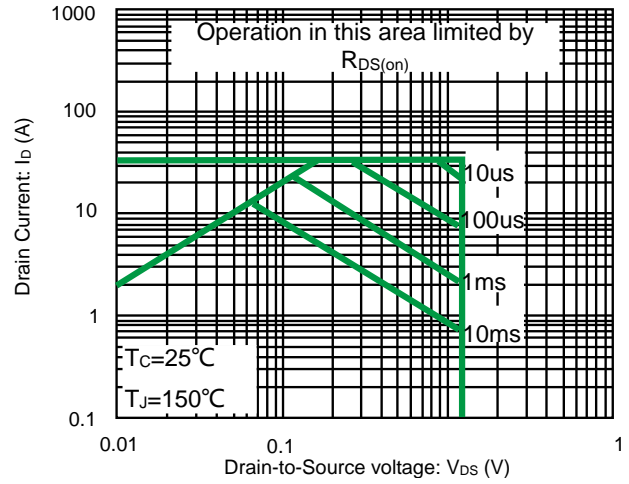


Fig 10. Maximum Safe Operating Area

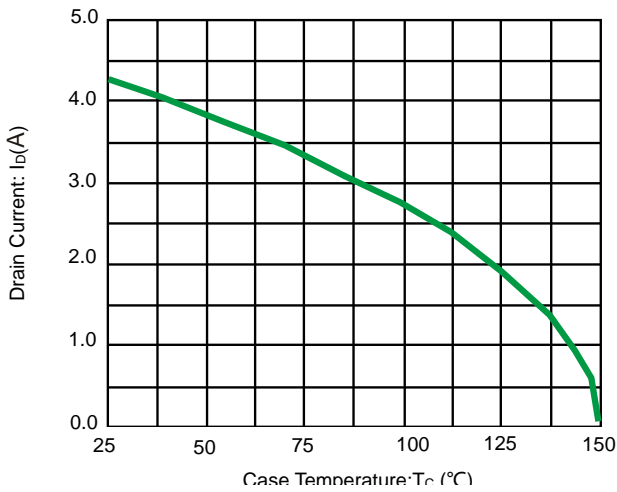


Fig 11. Maximum Drain Current vs. Case Temperature

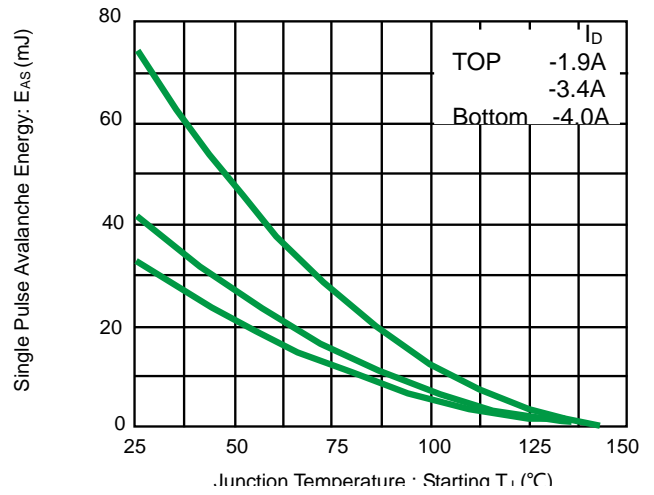


Fig 12. Maximum Avalanche Energy vs. Drain Current

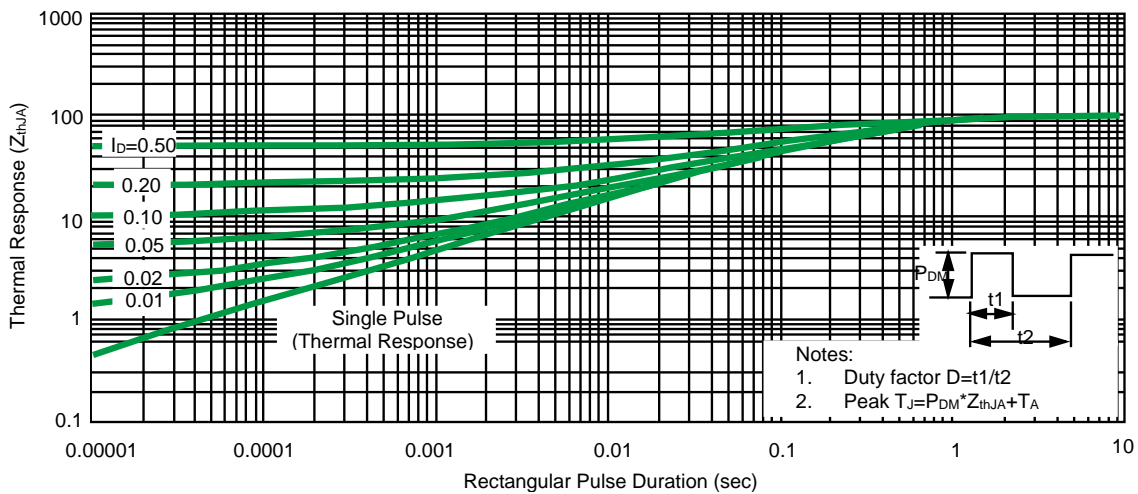


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

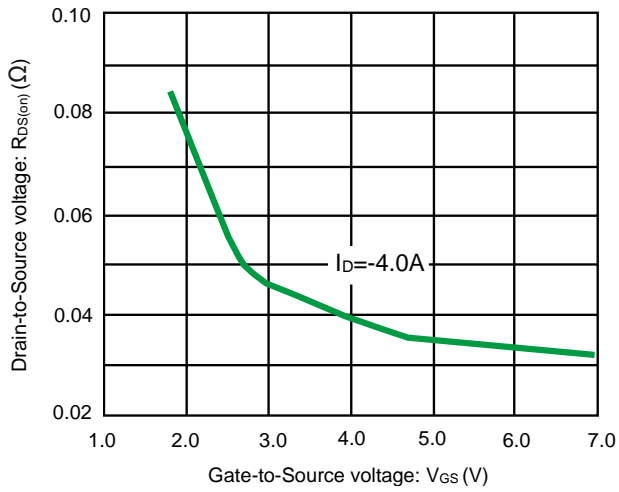


Fig 14. Typical On-Resistance vs. Gate Voltage

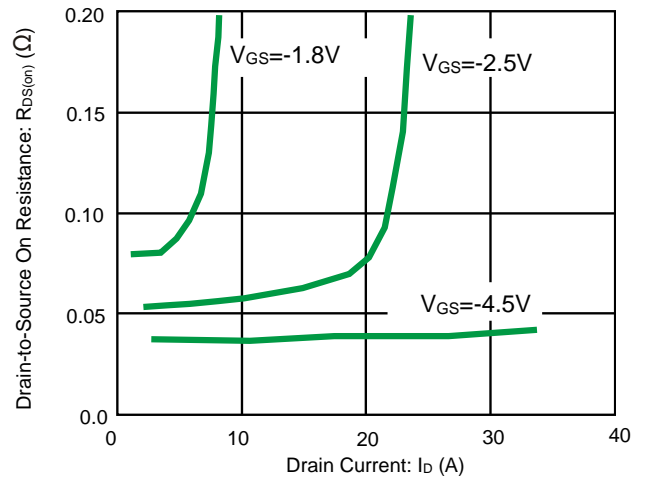


Fig 15. Typical On-Resistance vs. Drain Current

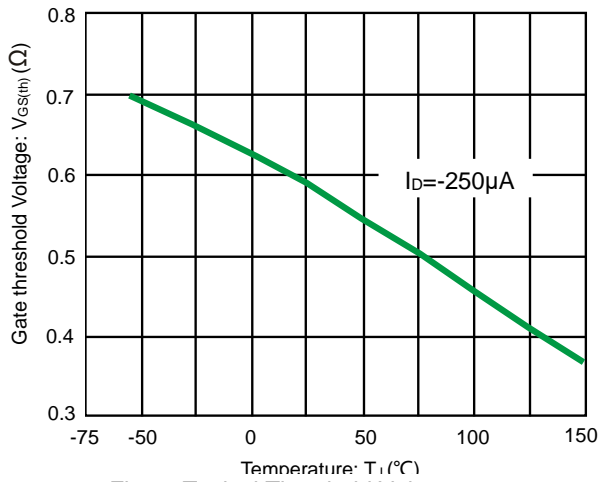
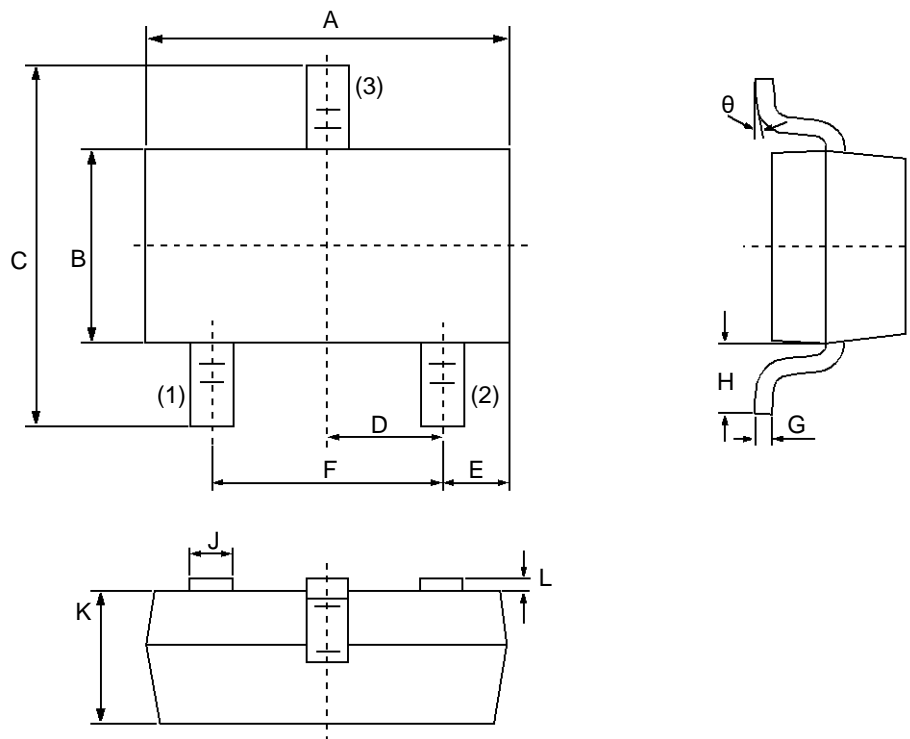
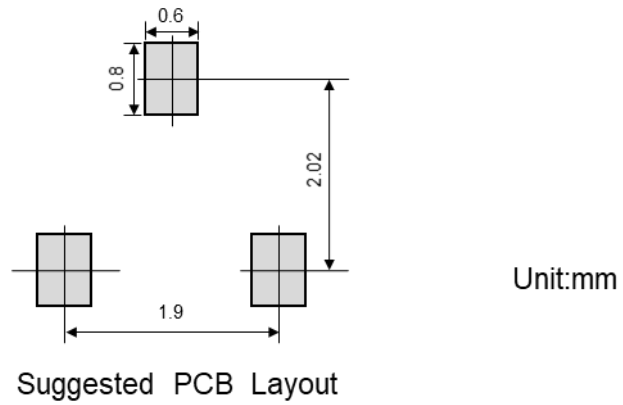


Fig16. Typical Threshold Voltage vs. Junction Temperature

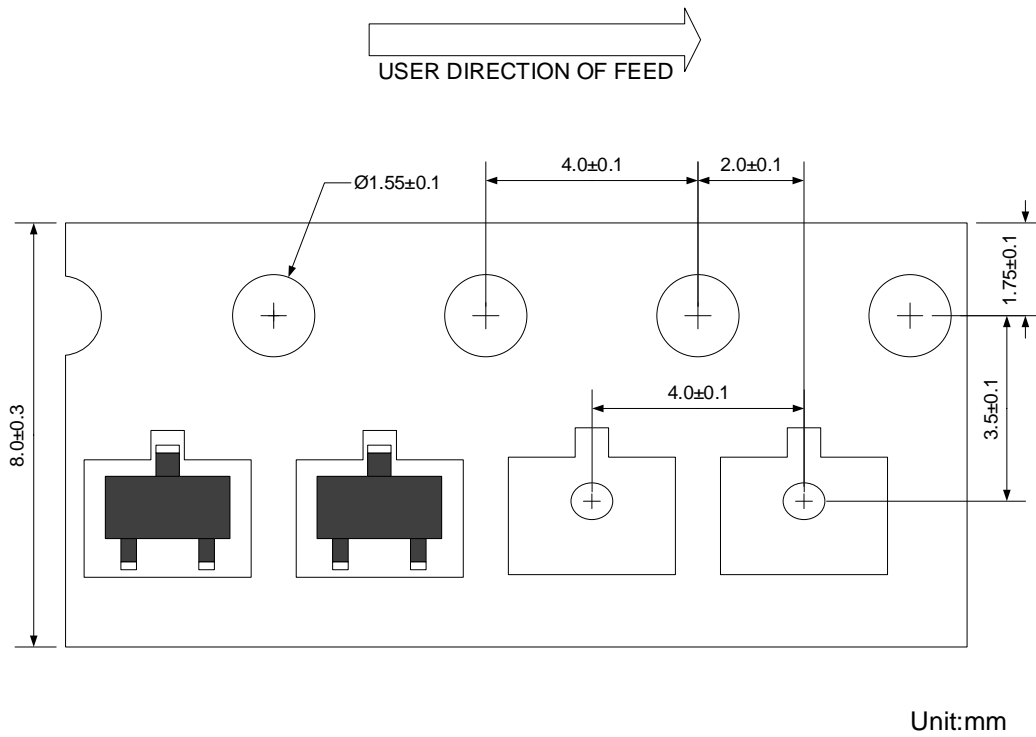
Product dimension(SOT-23)



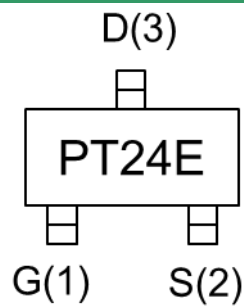
Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.80	3.00	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	2.10	2.50	0.0830	0.0984
D	0.89	1.02	0.0350	0.0401
E	0.45	0.60	0.0177	0.0236
F	1.78	2.04	0.0701	0.0807
G	0.085	0.177	0.0034	0.0070
H	0.45	0.60	0.0180	0.0236
J	0.37	0.50	0.0150	0.0200
K	0.89	1.11	0.0350	0.0440
L	0.013	0.100	0.0005	0.0040
θ	0°	10°	0°	10°



Load with information




Marking information



Ordering information

Device	Package	Reel	Shipping
PPMT20V4E	SOT-23 (Pb-Free)	7"	3000 / Tape & Reel


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